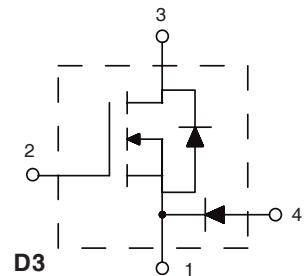
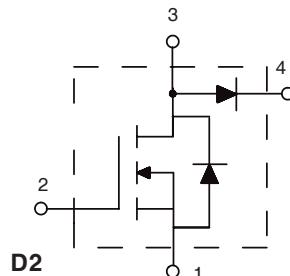


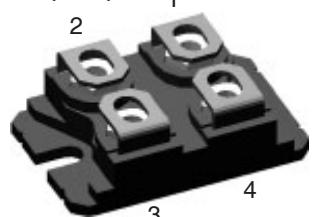
HiPerFET™
Power MOSFETs

	V_{DSS}	$I_{D(\text{cont})}$	$R_{DS(\text{on})}$	t_{tr}
IXFE44N50QD2	500 V	39 A	0.12 Ω	35 ns
IXFE48N50QD2	500 V	41A	0.11 Ω	35 ns

Buck & Boost Configurations for
PFC & Motor Control Circuits



	Symbol	Test Conditions	Maximum Ratings	
HiPerFET MOSFET	V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V
	V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	500	V
	V_{GS}	Continuous	± 20	V
	V_{GSM}	Transient	± 30	V
	I_{D25}	$T_c = 25^\circ\text{C}$	44N50Q	39 A
			48N50Q	41 A
	I_{DM}	$T_c = 25^\circ\text{C}$, pulse width limited by max. T_{JM}	44N50Q	176 A
			48N50Q	192 A
	I_{AR}	$T_c = 25^\circ\text{C}$	48	A
	E_{AR}	$T_c = 25^\circ\text{C}$	60	mJ
	E_{AS}	$T_c = 25^\circ\text{C}$	2.5	J
DIODE	dv/dt	$I_s \leq I_{DM}$, $-di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$	15	V/ns
	P_D	$T_c = 25^\circ\text{C}$	400	W
	V_{RRM}		600	V
	I_{FAVM}	$T_c = 70^\circ\text{C}$; rectangular, $d = 0.5$	60	A
	I_{FRM}	$tp < 10 \mu\text{s}$; pulse width limited by T_J	800	A
	P_D	$T_c = 25^\circ\text{C}$	180	W
	T_J		-40 ... +150	°C
	T_{JM}		150	°C
	T_{stg}		-40 ... +150	°C
	V_{ISOL}	50/60 Hz, RMS $t = 1 \text{ min}$ $I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$	2500	V~
CASE	M_d	Mounting torque Terminal connection torque (M4)	1.5/13 Nm/lb.in. 1.5/13 Nm/lb.in.	
	Weight		19	g

ISOPLUS 227™(IXFE)


2 = Gate

1 = Source

3 = Drain

4 = Anode/Cathode

Features

- Popular Buck & Boost circuit topologies
- Conforms to SOT-227B outline
- Isolation voltage 3000 V~
- Low $R_{DS(\text{on})}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Low drain-to-case capacitance (<60 pF)
 - reduced RFI
- Ultra-fast FRED diode with soft reverse recovery

Applications

- Power factor controls and buck regulators
- DC servo and robotic drives
- DC choppers
- Switch reluctance motor controls

Advantages

- Easy to mount with 2 screws
- Space savings
- Tightly coupled FRED

Symbol
Test Conditions
Characteristic Values
 $(T_J = 25^\circ C, \text{unless otherwise specified})$
min. **typ.** **max.**

V_{DSS}	$V_{GS} = 0 V, I_D = 1 mA$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 4 mA$	2		V
I_{GSS}	$V_{GS} = \pm 20 V_{DC}, V_{DS} = 0$		± 100	nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 V$	$T_J = 25^\circ C$ $T_J = 125^\circ C$	100 2	μA mA
$R_{DS(on)}$	$V_{GS} = 10 V, I_D = I_T$ 44N50Q 48N50Q Pulse test, $t \leq 300 \mu s$, duty cycle $\delta \leq 2\%$	44N50Q 48N50Q	0.12 0.11	Ω

Symbol
Test Conditions
Characteristic Values
 $(T_J = 25^\circ C, \text{unless otherwise specified})$
min. **typ.** **max.**

g_{fs}	$V_{DS} = 10 V, I_D = I_T$, pulse test	30	36	S
C_{iss} C_{oss} C_{rss}	$V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz$	8000 930 220		pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	$V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = I_T$ $R_G = 1\Omega$ (External)	33 22 75 10		ns
$Q_{g(on)}$ Q_{gs} Q_{gd}	$V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = I_T$	190 40 86		nC
R_{thJC} R_{thCK}			0.31 0.07	K/W

Ultra-fast Diode
Characteristic Values
 $(T_J = 25^\circ C, \text{unless otherwise specified})$
min. **typ.** **max.**

I_R	$T_J = 25^\circ C; V_R = V_{RRM}$ $T_J = 150^\circ C; V_R = 0.8V_{RRM}$		200 2.5	μA mA
V_F	$I_F = 60A, V_{GS} = 0 V$		2.05	V
	Note1	$T_J = 150^\circ C$	1.4	V
t_{rr}	$I_I = 1A, di/dt = -200 A/\mu s, V_R = 30 V, T_J = 25^\circ C$	35	50	ns
I_{RM}	$I_F = 60A, di/dt = -100 A/\mu s, V_R = 100 V, T_J = 100^\circ C$		8.3	A
R_{thJC}			0.7	K/W
R_{thCK}		0.05		K/W

 Note: 1. Pulse test, $t \leq 300 \mu s$, duty cycle $d \leq 2\%$

2. IXFE44N50
- $I_T = 22A$
-
- IXFE48N50
- $I_T = 24A$

IXYS reserves the right to change limits, test conditions, and dimensions.